



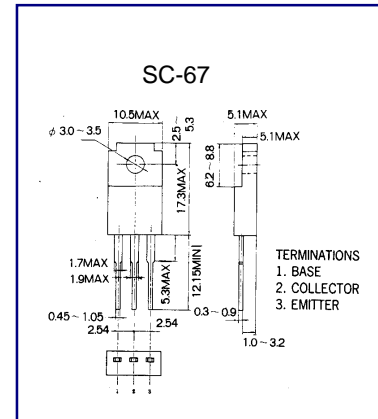
2SD1265

NPN EPITAXIAL SILICON TRANSISTOR

**POWER AMPLIFIER
VERTICAL DEFLECTION OUTPUT**

● **ABSOLUTE MAXIMUM RATINGS (T_A=25°C)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	60	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base voltage	V _{EB0}	5	V
Collector Current (DC)	I _C	4	A
Collector Dissipation (T _c =25°C)	P _C	30	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-50~150	°C



ELECTRICAL CHARACTERISTICS (T_A=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I _{CBO}	V _{CB} = 150V , I _E =0			10	μA
Emitter Cutoff Current	I _{EB0}	V _{EB} = 5V , I _C =0			10	μA
DC Current Gain	h _{FE1}	V _{CE} = 3.0V , I _C =-1.0A	70		240	
Collector- Emitter Saturation Voltage	V _{CE(sat)}	I _C =3A , I _B =-0.3mA			1.0	V
Current Gain Bandwidth Product	f _T	V _{CE} = -10V , I _C =-0.5A		60		MHZ